

# RJK5014DPK

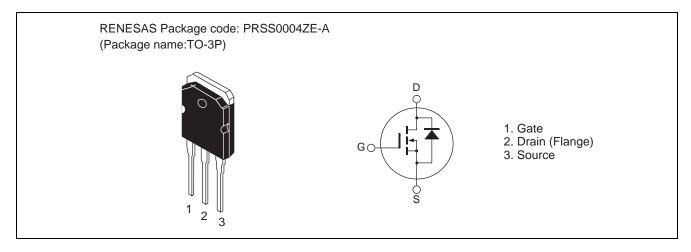
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1458-0200 Rev.2.00 Oct 20, 2009

#### **Features**

- Low on-resistance
- Low leakage current
- High speed switching

### **Outline**



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	500	V
Gate to source voltage	$V_{GSS}$	±30	V
Drain current	I <sub>D</sub>	19	А
Drain peak current	I <sub>D (pulse)</sub> Note1	38	А
Body-drain diode reverse drain current	I <sub>DR</sub>	19	А
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub> Note1	38	А
Avalanche current	I <sub>AP</sub> Note3	5	А
Avalanche energy	E <sub>AR</sub> Note3	1.3	mJ
Channel dissipation	Pch Note2	150	W
Channel to case thermal impedance	θch-c	0.833	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tc = 25°C
- 3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

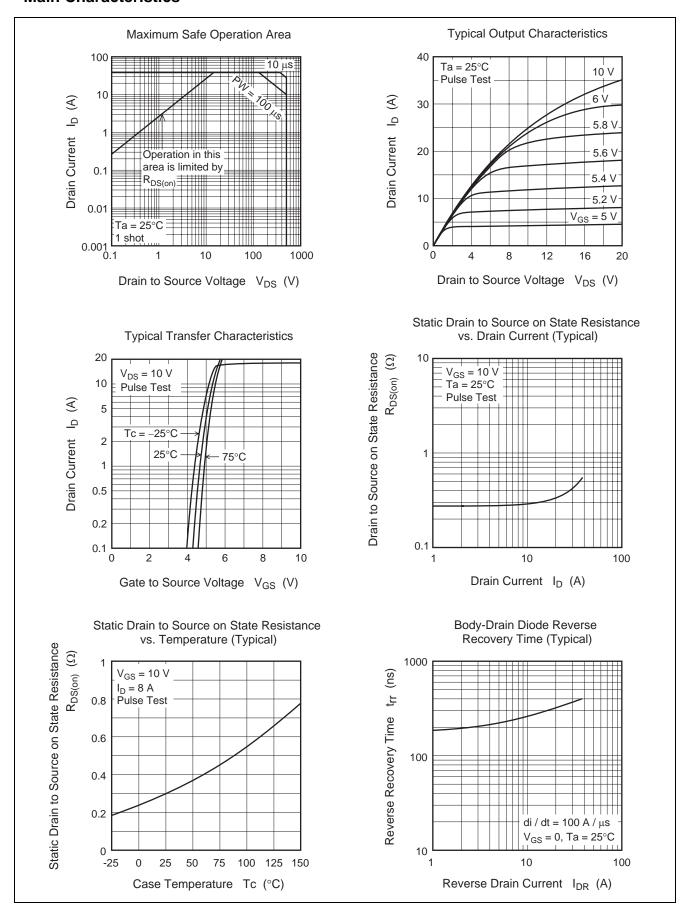
# **Electrical Characteristics**

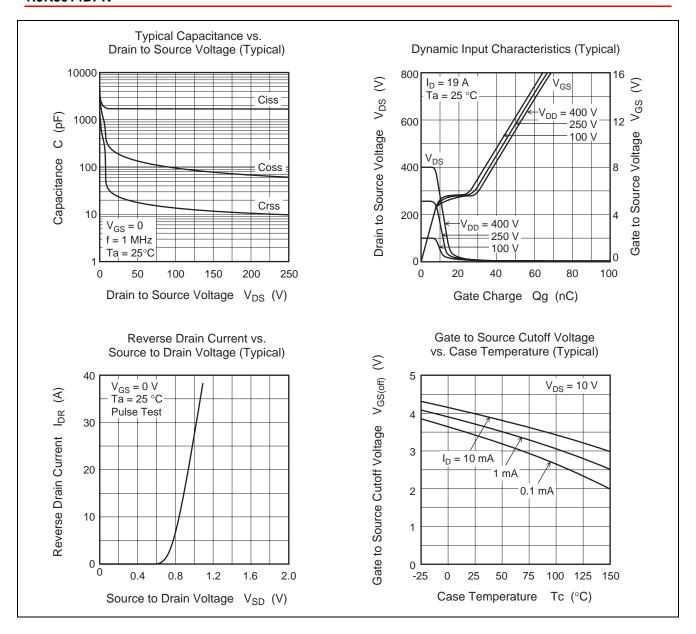
 $(Ta = 25^{\circ}C)$ 

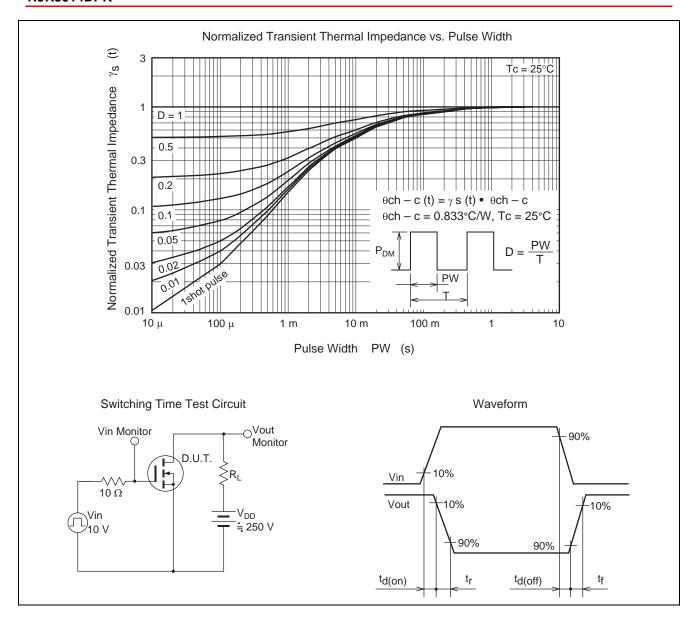
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500		_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>			1	μΑ	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>	l	0.315	0.380	Ω	$I_D = 9.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss		1800	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	190	_	pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	24	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	36	_	ns	I <sub>D</sub> = 9.5 A
Rise time	t <sub>r</sub>	_	41	_	ns	$V_{GS} = 10 \text{ V}$ $R_L = 26.3 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	$t_{d(off)}$	_	93	_	ns	
Fall time	t <sub>f</sub>	_	39	_	ns	
Total gate charge	Qg	_	46	_	nC	V <sub>DD</sub> = 400 V
Gate to source charge	Qgs	_	9	_	nC	V <sub>GS</sub> = 10 V I <sub>D</sub> = 19 A
Gate to drain charge	Qgd	_	20	_	nC	
Body-drain diode forward voltage	$V_{DF}$	_	0.91	1.55	V	$I_F = 19 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	320	_	ns	$I_F = 19 \text{ A}, V_{GS} = 0$ di <sub>F</sub> /dt = 100 A/ $\mu$ s

Notes: 4. Pulse test

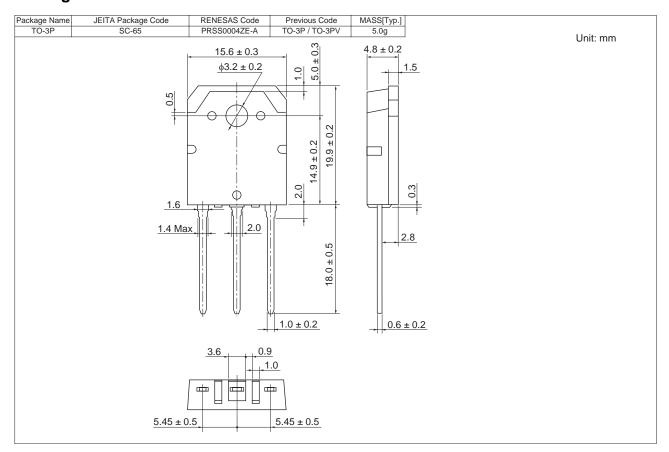
### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK5014DPK-00-T0	360 pcs	Box (Tube)

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